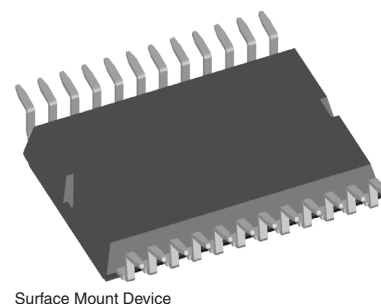


Three phase full Bridge

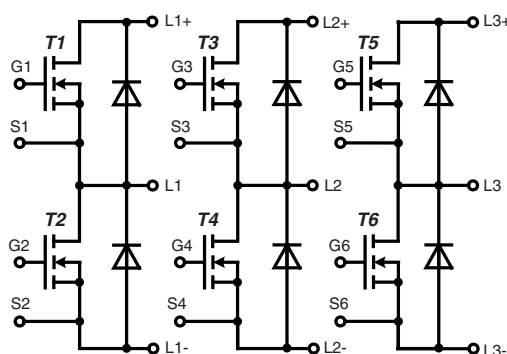
with Trench MOSFETs
in DCB isolated high current package

$V_{DSS} = 75\text{ V}$
 $I_{D25} = 255\text{ A}$
 $R_{DSon\text{ typ.}} = 1.1\text{ m}\Omega$

Part number
MTI200WX75GD



Surface Mount Device



Features / Advantages:

- MOSFETs in trench technology:
 - low R_{DSon}
 - optimized intrinsic reverse diode
- package:
 - high level of integration
 - high current capability
 - aux. terminals for MOSFET gate control
 - terminals for soldering or welding connections
 - isolated DCB ceramic base plate with optimized heat transfer
- Space and weight savings
- High current capability

Applications:

- AC drives
 - in automobiles
 - electric power steering
 - starter generator
 - in industrial vehicles
 - propulsion drives
 - fork lift drives
- Battery supplied equipment
- DC-DC converter

Package: ISOPLUS-DIL®

- High level of integration
- RoHS compliant
- Terminals for soldering or welding connections
- Space and weight savings
- High reliability
- Low thermal impedance

Terms & Conditions of usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments;

- the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, test conditions and dimensions.

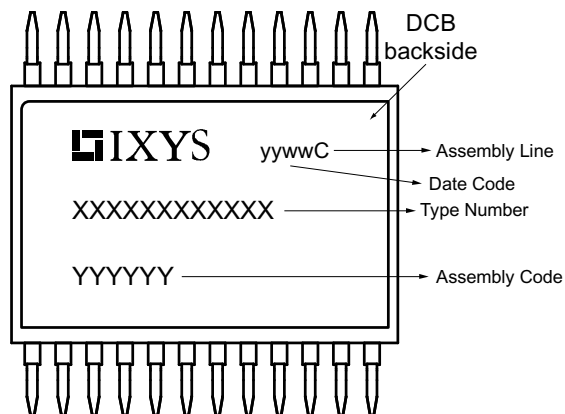
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1 - 7

| MOSFETs | | | | Ratings | | | |
|---|---|--|-------------------------|------------|----------|----------|--|
| Symbol | Definitions | Conditions | min. | typ. | max. | Unit | |
| V _{DSS} | drain source breakdown voltage | T _{VJ} = 25°C to 150°C | | | 75 | V | |
| V _{GS} | max. DC gate source voltage | | | | ±15 | V | |
| V _{GSM} | max. transient gate source voltage | | | | ±20 | V | |
| I _{D25} | continuous drain current | T _C = 25°C | | | 255 | A | |
| I _{D90} | (die capability) | T _C = 90°C | | | 190 | A | |
| R _{DS(on)} ¹⁾ | static drain source on resistance | on chip level at I _D = 100 A; V _{GS} = 10 V | | 1.1 1.8 | 1.3 | mΩ mΩ | |
| V _{GS(th)} | gate threshold voltage | I _D = 275 μA; V _{DS} = V _{GS} | 2.3 | 3.1 | 3.8 | V | |
| I _{DSS} | drain source leakage current | V _{DS} = V _{DSS} ; V _{GS} = 0 V | | 10 | 1 100 | μA μA | |
| I _{GSS} | gate source leakage current | V _{GS} = ±20 V; V _{DS} = 0 V | | | 500 | nA | |
| R _G | gate resistance | on chip | | 2.7 | | Ω | |
| C _{iss} | input capacitance | V _{GS} = 0 V; V _{DS} = 38 V; f = 1 Mhz | | 10.8 | 14.4 | nF | |
| C _{oss} | output capacitance | | | 2.42 | 3.22 | nF | |
| C _{rss} | reverse transfer capacitance | | | 110 | - | pF | |
| Q _g | total gate charge | V _{GS} = 10 V; V _{DS} = 38 V; I _D = 100 A | | 155 | | nC | |
| Q _{gs} | gate source charge | | | 53 | | nC | |
| Q _{gd} | gate drain (Miller) charge | | | 32 | | nC | |
| t _{d(on)} | turn-on delay time | inductive load V _{GS} = 10 V; V _{DS} = 30 V I _D = 100 A; R _G = 27 Ω T _{VJ} = 125°C | | 145 | | ns | |
| t _r | current rise time | | | 70 | | ns | |
| t _{d(off)} | turn-off delay time | | | 520 | | ns | |
| t _f | current fall time | | | 55 | | ns | |
| E _{on} | turn-on energy per pulse | | | 80 | | μJ | |
| E _{off} | turn-off energy per pulse | | | 350 | | μJ | |
| E _{rec(off)} | turn-off reverse recovery losses | | | 8 | | μJ | |
| R _{thJC} | thermal resistance junction to case | | | | 0.85 | K/W | |
| R _{thJH} | thermal resistance junction to heatsink | with heat transfer paste (IXYS test setup) | | 1.1 | 1.4 | K/W | |
| ¹⁾ V _{DS} = I _D •(R _{DS(on)} + 2•R _{PIn to Chip}) | | | | | | | |
| Source-Drain Diode | | | | | | | |
| I _{F25} | forward current (body diode) | V _{GS} = 0 V | T _C = 25°C | | 175 | A | |
| I _{F90} | | | T _C = 90°C | | 100 | A | |
| V _{SD} | source drain voltage | I _F = 100 A; V _{GS} = 0 V | T _{VJ} = 25°C | 0.9 | 1.2 | V | |
| Q _{RM} | reverse recovery charge | V _R = 30 V; I _F = 100 A R _G = 27 Ω | T _{VJ} = 125°C | 730 | | nC | |
| I _{RM} | max. reverse recovery current | | | 27 | | A | |
| t _{rr} | reverse recovery time | | | 42 | | ns | |

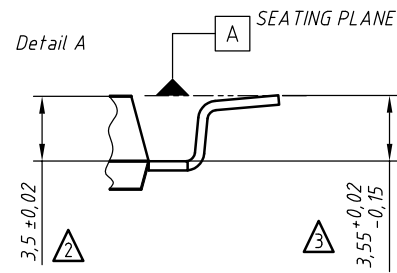
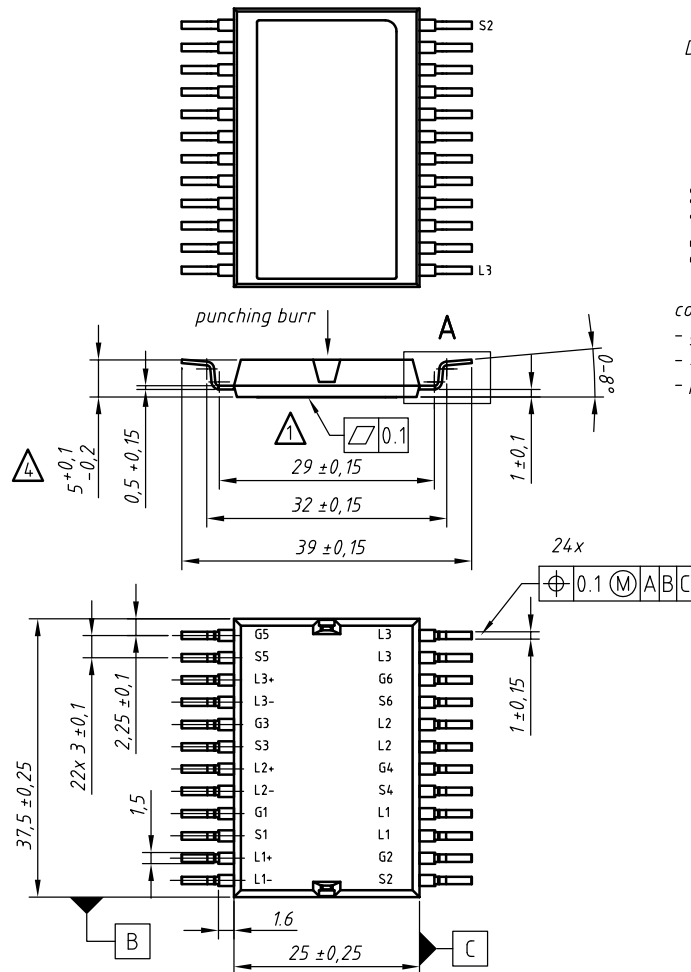
| Package ISOPLUS-DIL® | | | Ratings | | |
|----------------------|------------------------------|---|---------|------|-----------|
| Symbol | Definitions | Conditions | min. | typ. | max. Unit |
| I_{RMS} | RMS current | per pin in main current paths (L1+...L3+, L1-...L3-, L1...L3) may be additionally limited by external connections (PCB tracks) 2 pins for output L1, L2, L3 | | | 75 A |
| T_{stg} | storage temperature | | -55 | | 125 °C |
| T_{op} | operation temperature | | -55 | | 150 °C |
| T_{vj} | virtual junction temperature | | -55 | | 175 °C |
| Weight | | | | 13 | g |
| F_C | mounting force with clip | | 50 | | 250 N |
| V_{ISOL} | isolation voltage | $t = 1$ second | 1200 | | V |
| | | $t = 1$ minute | | | |
| | | 50/60 Hz, RMS, $I_{ISOL} \leq 1$ mA | 1000 | | V |
| $R_{pin-chip}$ | resistance terminal to chip | $V_{DS} = I_D \cdot (R_{DS(on)} + 2 \cdot R_{pin\ to\ chip})$ | | 0.5 | mΩ |
| C_P | coupling capacity | between shorted pins and back side metallization | | 160 | pF |

**Part number**

M = MOSFET
 T = Trench
 I = Infineon Trench
 200 = Current Rating [A]
 WX = 6-Pack with separated phase legs
 75 = Reverse Voltage [V]
 GD = ISOPLUS-DIL

| Ordering | Part Name | Marking on Product | Delivering Mode | Base Qty | Ordering Code |
|----------|------------------|--------------------|-----------------|----------|---------------|
| Standard | MTI200WX75GD-SMD | MTI200WX75GD | Tube | 13 | 516955 |

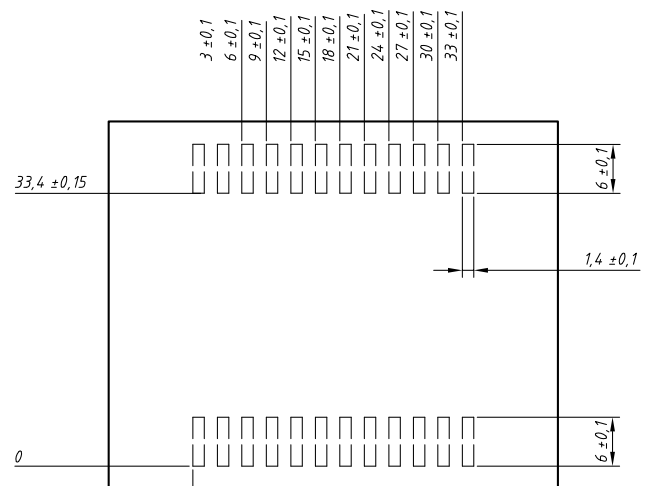
Outlines ISOPLUS-DIL®



contact pin:

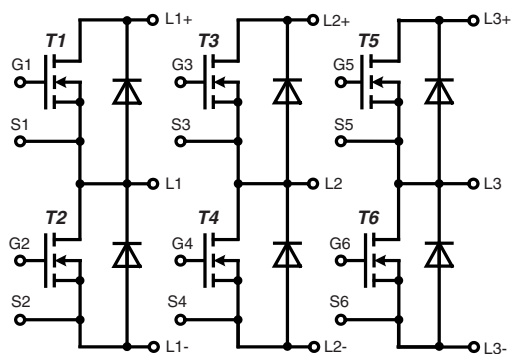
- galv. tin plating, per pin side: Sn 10...25 µm, undercoating Ni 0,2...1 µm
- stamping edges may be free of tin
- punching burr: ≤ 0,05mm

- 1 Convex bow of substrate, typ. 10-40 µm longitudinal and 5-15 µm transversal
- 2 Distance between pin and case bottom side.
- 3 Distance between pin and contact surface.
- 4 Distance between parallel planes aligned to top and bottom sides of the package



Remarks:

- 1) pin layout / dimensions are conditionally
- 2) soldering paste thickness: 200µm



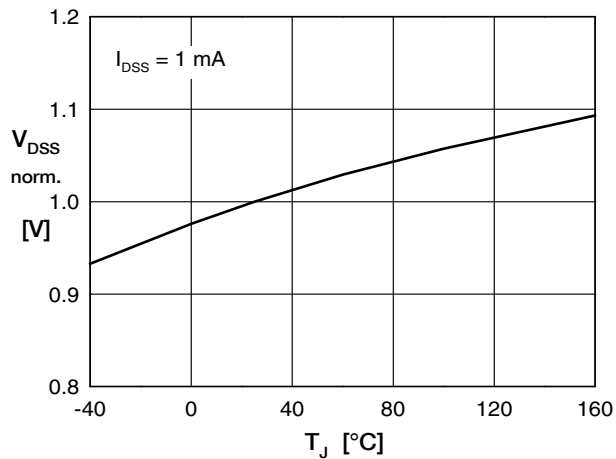


Fig.1 Drain source breakdown voltage V_{DSS} vs. junction temperature T_{VJ}

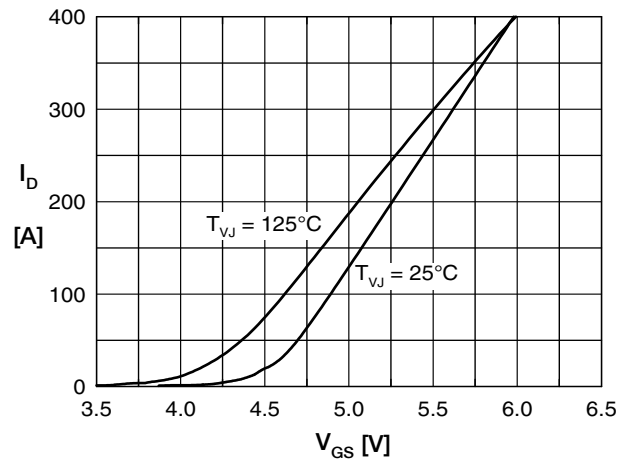


Fig. 2 Typ. transfer characteristics

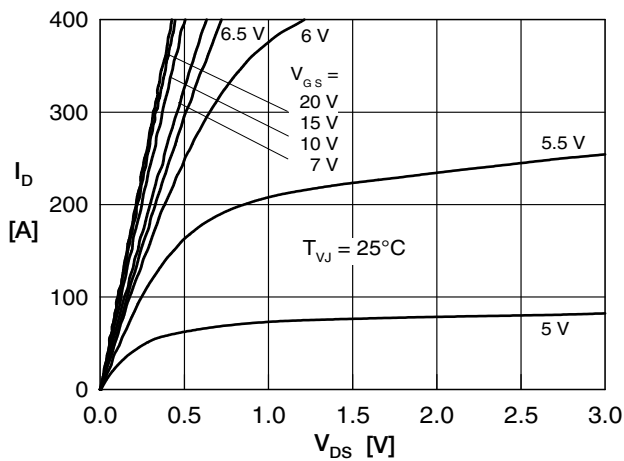


Fig. 3 Typ. output characteristics on die level

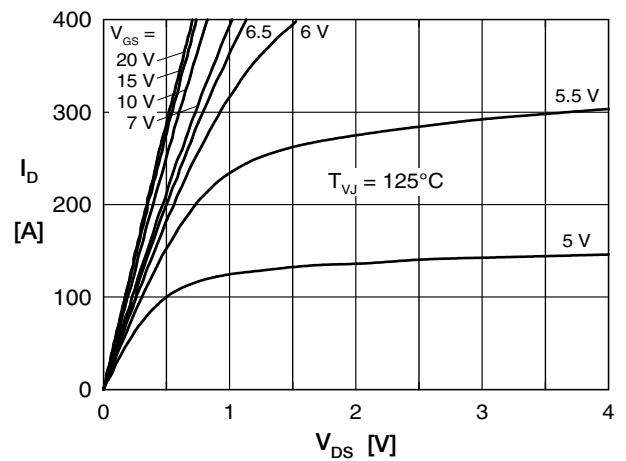


Fig. 4 Typ. output characteristics on die level

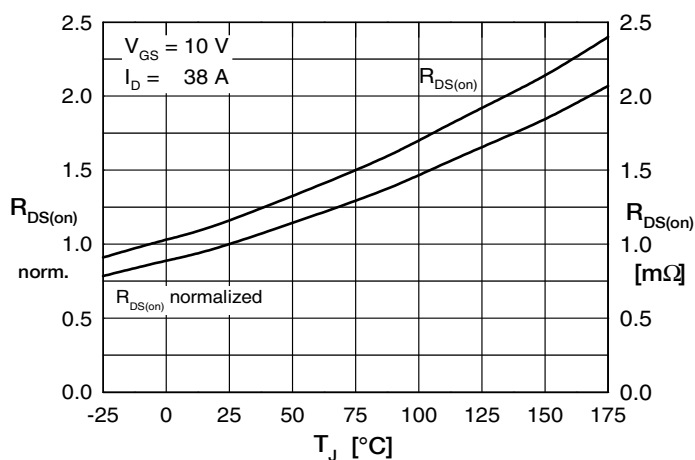


Fig.5 Drain source on-state resistance $R_{DS(on)}$ vs. junction temperature T_{VJ} , on die level

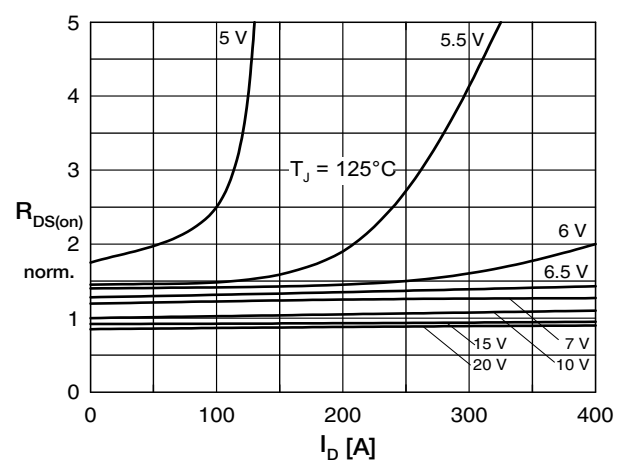


Fig. 6 Drain source on-state resistance $R_{DS(on)}$ versus I_D , on die level

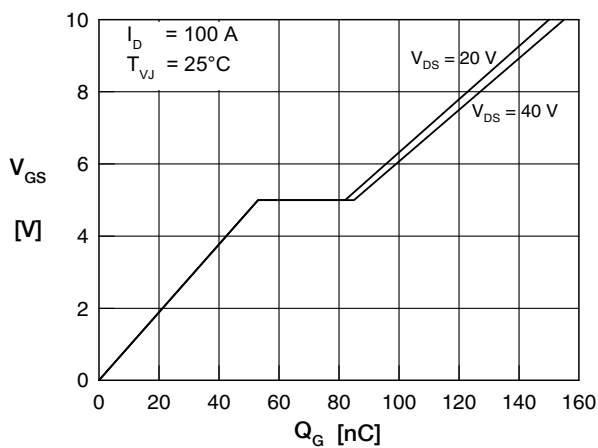


Fig. 7 Typical turn on gate charge

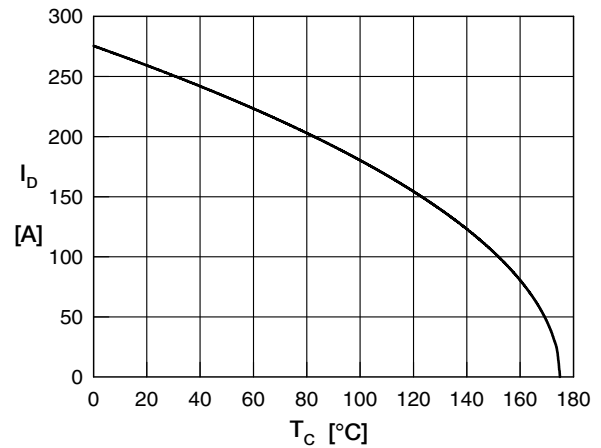


Fig. 8 Drain current I_D vs. case temperature T_C (Chip capability)

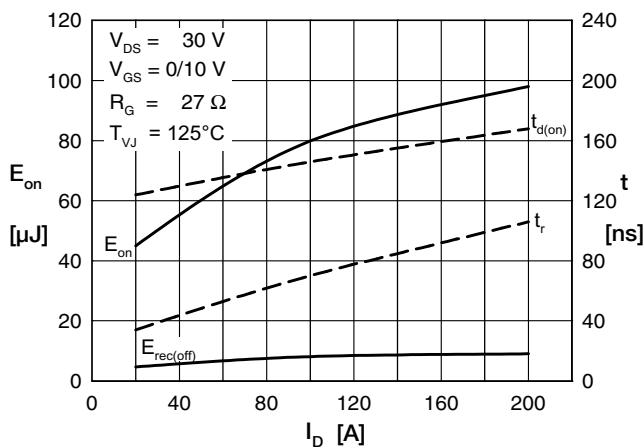


Fig. 9 Typ. turn-on energy and switching times versus drain current, inductive switching

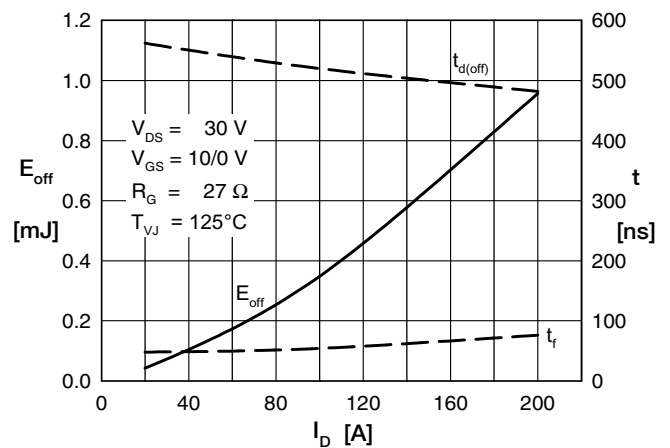


Fig. 10 Typ. turn-off energy and switching times versus drain-current, inductive switching

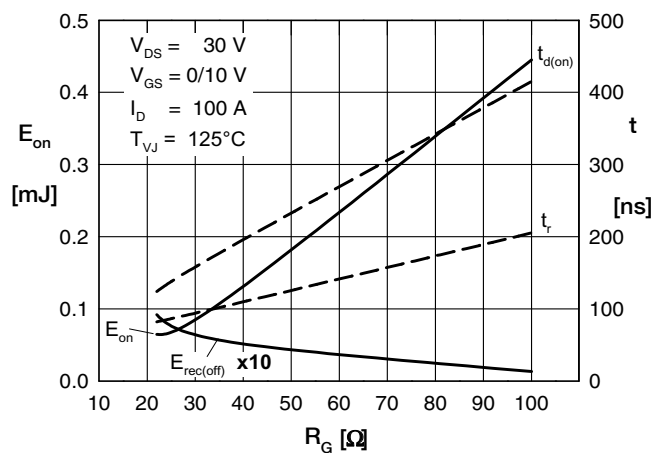


Fig. 11 Typ. turn-on energy and switching times versus gate resistor, inductive switching

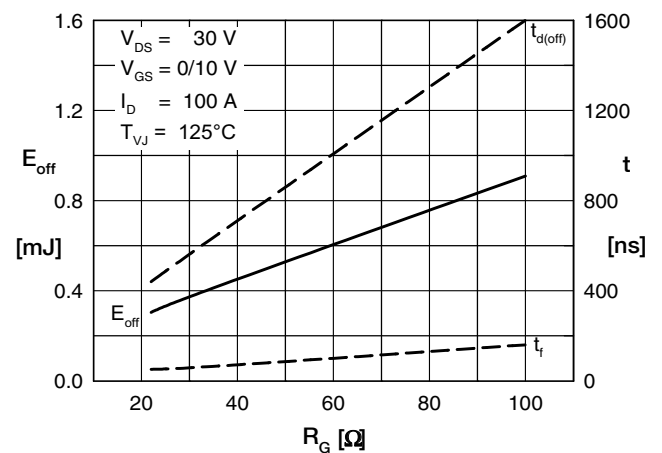


Fig. 12 Typ. turn-off energy and switching times versus gate resistor, inductive switching

